

# Magnetotransport and Dielectric Properties of Bi-Containing $\text{La}_{0.6}\text{Sr}_{0.15}\text{Bi}_{0.15}\text{Mn}_{1.1-x}\text{B}_x\text{O}_{3-\delta}$ Rare-Earth Manganites with $B = \text{Cr}, \text{Fe}, \text{Co}, \text{Ni}$

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**Abstract**— The effect of the replacement of manganese by 3d-ions of transition metals on the structural, microstructural, dielectric, and magnetotransport properties of nonstoichiometric  $\text{La}_{0.6}\text{Sr}_{0.15}\text{Bi}_{0.15}\text{Mn}_{1.1-x}\text{B}_x\text{O}_{3-\delta}$  compositions with  $B = \text{Cr}, \text{Fe}, \text{Co}$  and  $\text{Ni}$  ( $0 \leq x \leq 0.3$ ) was investigated. It is shown that in all compositions a weak change for the lattice parameter of the rhombohedral perovskite structure is observed. It is established that the real structure is defective and contains cationic  $\text{V}^{(c)}$  and anionic  $\text{V}^{(a)}$  vacancies. With increasing  $x$ , an increase in the resistivity and the absence of a metal-semiconductor phase transition for  $x > 0.20$  are observed. The electron-phonon interaction constant  $\gamma_{ph}$  was determined. The most significant change in the structural and functional properties was observed for the compositions with  $B = \text{Fe}$ , for which constant  $\gamma_{ph} \approx 7.7$  achieves a maximum value. At  $x = 0.05$ , an increase in magnetoresistance effect of the tunnel type is observed.

**Keywords**— structural defectiveness; electronic transport; dielectric constant; electron-phonon interaction constant; magnetoresistance effect

## I. INTRODUCTION

Increased interest both in terms of fundamental and applied aspects of science arises in the study and synthesis of multifunctional materials which simultaneously have high values of the colossal magnetoresistance (MR) effect, magnetization, Curie temperature  $T_C$  and at the same time exhibit dielectric properties [1-3]. Such materials include Bi-containing rare-earth (RE) manganites with the structure of perovskite, in which a large number of phase transitions coexistences with competing types of interactions [2, 4, 5].

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We have established that  $\text{La}_{0.6}\text{Sr}_{0.15}\text{Bi}_{0.15}\text{Mn}_{1.1}\text{O}_{3-\delta}$  composition is optimal with the largest value of spontaneous magnetization and the magnitude of the MR effect near  $T_C$ .

The particular interest is the study of the effect of substitutions of  $B$  cations of manganese for the 3d-ions of the transition metals Cr, Fe, Co, and Ni on the formation of functional properties of Bi-containing RE manganites. The investigation of the structure and its defectiveness as well as microstructural, dielectric, transport and MR properties of the nonstoichiometric  $\text{La}_{0.6}\text{Sr}_{0.15}\text{Bi}_{0.15}\text{Mn}_{1.1-x}\text{B}_x\text{O}_{3-\delta}$  compositions with  $B = \text{Cr}, \text{Fe}, \text{Co}$  and  $\text{Ni}$  ( $0 \leq x \leq 0.3$ ) causes the relevance of this work.

## II. OBJECTS AND RESEARCH METHODS

Synthesis of powders of all compositions was carried out by the conventional solid-state reaction method in two-stage from the corresponding carefully mixed stoichiometric mixtures of  $\text{La}_2\text{O}_3$ ,  $\text{SrO}$ ,  $\text{Bi}_2\text{O}_3$ ,  $\text{MnO}_2$ ,  $\text{Cr}_2\text{O}_3$ ,  $\text{Fe}_2\text{O}_3$ ,  $\text{Co}_3\text{O}_4$  and  $\text{NiO}$  powders (purity > 99 %) at  $t_{synth} = 800^\circ\text{C}$  (18 h) and  $850^\circ\text{C}$  (18 h). Ceramics  $\text{La}_{0.6}\text{Sr}_{0.15}\text{Bi}_{0.15}\text{Mn}_{1.1-x}\text{B}_x\text{O}_{3-\delta}$  for  $B = \text{Cr}, \text{Fe}, \text{Co}, \text{Ni}$  with  $x = 0, 0.05, 0.1, 0.15, 0.2, 0.25, 0.3$  were obtained from the synthesized powder with its repeated grinding, pressing into pellets under  $P = 0.2 \text{ GPa}$  and annealing at  $t_{ann} = 1000^\circ\text{C}$  (18 h) in the mode of slow heating and cooling in air. To study the structure and its defectiveness, as well as microstructural, dielectric, transport and MR properties of the ceramics the following experimental methods were used:

- X-ray diffraction (PANalitical X-Pert PRO MRD diffractometer) to determine the type of crystalline structure, phase composition and lattice parameters;
- thermogravimetric to determine the relative changes of mass loss of samples and the structure defects;
- iodometric titration to determine oxygen index and the average valence of manganese ions;
- scanning electron microscopy (SEM);
- four-probe resistance to determine resistivity and magnetoresistance effect;
- dielectric spectroscopy to determine relative dielectric permittivity.

### III. RESULTS AND DISCUSSION

According to X-ray diffraction data, all ceramic samples  $\text{La}_{0.6}\text{Sr}_{0.15}\text{Bi}_{0.15}\text{Mn}_{1.1-x}B_x\text{O}_{3-\delta}$  with  $B = \text{Cr}, \text{Fe}, \text{Co}$  and  $\text{Ni}$  were single-phase with weakly changing lattice parameter of  $R\bar{3}c$  rhombohedral distorted perovskite structure.

On the basis of the defect formation mechanism [6] it was established that the real structure  $\text{La}_{0.6}\text{Sr}_{0.15}\text{Bi}_{0.15}\text{Mn}_{1.1-x}B_x\text{O}_{3-\delta}$  with  $B = \text{Cr}, \text{Fe}, \text{Co}$  and  $\text{Ni}$  is defective and contains anionic  $V^{(a)}$  and cationic  $V^{(c)}$  vacancies as well as manganese ions  $\text{Mn}^{3+}$  and  $\text{Mn}^{4+}$  in the  $B$ -positions, whose concentration depends on the replacement  $3d$ -ion  $B = \text{Cr}^{3+}, \text{Fe}^{3+}, \text{Co}^{2+}(\text{Co}^{\text{III}}), \text{Ni}^{2+}$ . For all compositions with increasing  $x$ , an increase in the concentration of anionic  $V^{(a)}$  vacancies from  $V^{(a)} = 6.3\%$  ( $x = 0$ ) to  $7.3\%$  ( $x = 0.3$ ),  $8.3\%$  ( $x = 0.3$ ),  $8.7\%$  ( $x = 0.3$ ) and  $10.3\%$  ( $x = 0.3$ ) is observed for  $B = \text{Cr}, \text{Fe}, \text{Co}$  and  $\text{Ni}$ , respectively.

The temperature dependences of the resistivity  $\rho(T)$  of  $\text{La}_{0.6}\text{Sr}_{0.15}\text{Bi}_{0.15}\text{Mn}_{1.1-x}B_x\text{O}_{3-\delta}$  samples with  $B = \text{Cr}, \text{Fe}, \text{Co}$  and  $\text{Ni}$  (Fig. 1) show that the temperature of the metal-semiconductor phase transition  $T_{\text{ms}}$  decreases with increasing  $x$  from  $T_{\text{ms}} = 205\text{ K}$  ( $x = 0$ ) to  $124\text{ K}$  ( $x = 0.15$ ),  $150\text{ K}$  ( $x = 0.05$ ) and  $122\text{ K}$  ( $x = 0.15$ ) for  $B = \text{Cr}, \text{Fe}$ , and  $\text{Co}$ , respectively. The resistivity  $\rho$  at  $T_{\text{ms}}$  increases with increasing concentration of  $3d$ -ions Cr, Fe, and Co from  $\rho(T_{\text{ms}}) = 1.7\text{ Ohm}\cdot\text{cm}$  ( $x = 0$ ) to  $43.8\text{ Ohm}\cdot\text{cm}$  ( $x = 0.15$ ),  $14.0\text{ Ohm}\cdot\text{cm}$  ( $x = 0.05$ ) and  $15.5\text{ Ohm}\cdot\text{cm}$  ( $x = 0.15$ ), respectively. The composition with the replacement of Mn by Fe ions has higher values of the resistivity in comparison with  $B = \text{Cr}, \text{Co}$  and  $\text{Ni}$  (Fig. 2 a).

A decrease in  $T_{\text{ms}}$  and an increase in  $\rho$  with an increase in  $x$  as well as the absence of the metal-semiconductor phase transition for compositions with  $x > 0.2$  are due to weakening of the double exchange  $\text{Mn}^{3+} \leftrightarrow \text{O}^{2-} \leftrightarrow \text{Mn}^{4+}$  by point defects of the vacancy type  $\text{Mn}^{3+} \leftrightarrow \text{O}^{2-} \leftrightarrow \text{Mn}^{4+} \leftrightarrow V^{(a)} \leftrightarrow \text{Mn}^{3+}$  and  $3d$ -ions of the transition metals  $\text{Mn}^{3+} \leftrightarrow \text{O}^{2-} \leftrightarrow B \leftrightarrow \text{O}^{2-} \leftrightarrow \text{Mn}^{4+}$  with  $B = \text{Cr}^{3+}, \text{Fe}^{3+}, \text{Co}^{2+}, \text{Co}^{\text{III}}$  and  $\text{Ni}^{2+}$ .

Of particular interest are the transport properties of RE manganites in the paramagnetic semiconductor region at  $T > T_{\text{ms}}$  and  $T_C$ . The most suitable conduction mechanism in the high-temperature region, as was shown in works [7], is the thermally activated process of the hopping conductivity of a small polaron for the Mott and Davis model [8]:

$$\rho/T^n = \rho_0 \cdot \exp(E_\rho/k_B T), \quad (1)$$

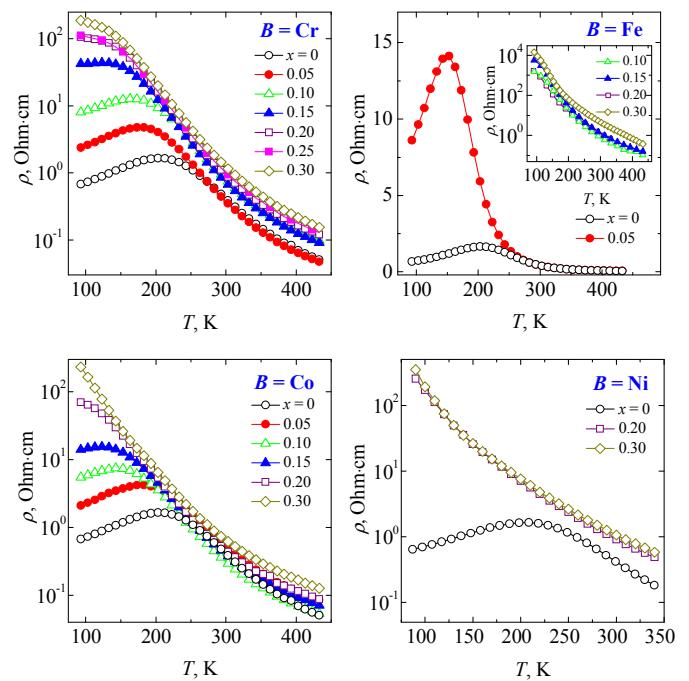


Fig. 1. Temperature dependences of resistivity of  $\text{La}_{0.6}\text{Sr}_{0.15}\text{Bi}_{0.15}\text{Mn}_{1.1-x}B_x\text{O}_{3-\delta}$  ceramics with  $B = \text{Cr}, \text{Fe}, \text{Co}, \text{Ni}$ .

where  $\rho_0 = [k_B/v_{\text{ph}}Ne^2R^2C(1-C)] \cdot \exp(2\alpha R)$ ;  $n$  is the exponent with a temperature factor for the adiabatic ( $n = 1$ ) and non-adiabatic ( $n = 1.5$ ) processes;  $k_B$  is the Boltzmann constant;  $T$  is the absolute temperature;  $N$  is the number of  $e_g$ -electrons  $\text{Mn}^{3+}$ , per unit volume, obtained from X-ray diffraction data taking into account structural defectiveness;  $R = (1/N)^{1/3}$  is the average distance between the centers of the polarons;  $C$  is share of occupied positions by a polaron;  $\alpha$  is the damping constant of the electron wave function;  $v_{\text{ph}}$  is the optical phonon frequency, determined from the relation  $hv_{\text{ph}} = k_B\theta_D$ , where  $\theta_D$  is the Debye temperature.

The activation energy is determined by [8]:

$$E_\rho = \begin{cases} W_H + W_D / 2, & \text{for } T > \theta_D / 2 \text{ and } n = 1 \\ W_D, & \text{for } T < \theta_D / 4 \text{ and } n = 1.5 \end{cases}, \quad (2)$$

where  $W_D$  is the energy difference between the two polaron states (disorder energy) and  $W_H$  is the polaron hopping energy.

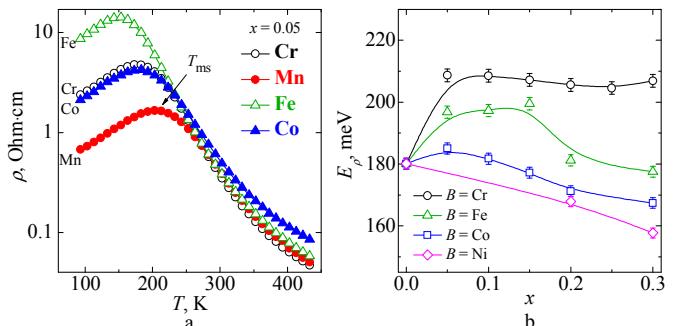


Fig. 2. Comparative analysis of the temperature dependences of the resistivity for  $x = 0.05$  (a) and concentration dependences of the activation energy for all  $x$  (b) of  $\text{La}_{0.6}\text{Sr}_{0.15}\text{Bi}_{0.15}\text{Mn}_{1.1-x}B_x\text{O}_{3-\delta}$  ceramics  $B = \text{Cr}, \text{Fe}, \text{Co}, \text{Ni}$ .

To determine the activation energy  $E_\rho$  (see Table I), in the paramagnetic of the semiconductor region at  $T > \theta_D/2$ , considering the best linear approximation of the experimental values of the resistivity  $\ln(\rho/T) = f(1/T)$ , it was used adiabatic process with exponent  $n = 1$  in equation (1). The deviation from the linear dependence  $\ln(\rho/T) = f(1/T)$  corresponded to the temperature  $T = \theta_D/2$ . The concentration dependences of  $E_\rho$  for all compositions shown in Fig. 2b. The nonmonotonic increase of  $E_\rho$  with increasing  $x$  for compositions with  $B = \text{Cr}$  and  $\text{Fe}$  is observed. The decrease of  $E_\rho$  with increasing  $x$  for compositions with  $B = \text{Co}$  and  $\text{Ni}$  can be explained by the appearance of more conductive subsystems  $\text{Co}^{2+} \leftrightarrow \text{O}^{2-} \leftrightarrow \text{Mn}^{4+}$  and  $\text{Ni}^{2+} \leftrightarrow \text{O}^{2-} \leftrightarrow \text{Mn}^{4+}$ , discussed in works [9, 10].

In the low-temperature region, at  $T < \theta_D/4$ , the activation energy  $E_\rho = W_D$  was determined for a nonadiabatic process with  $n = 1.5$  in expression (1). Based on the experimentally determined parameters (see Table I), the polaron hopping energy  $W_H$  from the system of equations (2), the electron-phonon interaction constant  $\gamma_{\text{ph}} = 2W_H/hv_{\text{ph}}$  and the polaron radius  $r_p$  from the relation  $W_H = e^2/4\epsilon'(1/r_p - 1/R)$  were calculated. The  $\epsilon'$  is a high-frequency relative permittivity which was measured in the microwave range  $f = 8.15-78.33$  GHz.

As can be seen from Table I, for all compositions with  $B = \text{Cr}, \text{Fe}, \text{Co}$ , and  $\text{Ni}$ , as the  $x$  increases, the Debye temperature  $\theta_D$  and the hopping frequency  $v_{\text{ph}}$  decrease. A small change in the polaron radius  $r_p$  and the high-frequency relative permittivity  $\epsilon'$  with increase in  $x$  is observed. The high values of the electron-phonon interaction constant  $\gamma_{\text{ph}} > 4$  [8] indicate a partial localization of  $e_g$ -electrons of manganese ions as a result of the attenuation of the double exchange of  $\text{Mn}^{3+}(3d^4) \leftrightarrow \text{O}^{2-}(2p^6) \leftrightarrow \text{Mn}^{4+}(3d^3)$  with manganese replacement by  $3d$ -ions of transition metals  $\text{Cr}^{3+}, \text{Fe}^{3+}, \text{Co}^{2+}, \text{Co}^{\text{III}}, \text{Ni}^{2+}$  and the increase in point defects of the vacancy type.

An additional confirmation of the existence of a small polaron for all compositions with  $B = \text{Cr}, \text{Fe}, \text{Co}$ , and  $\text{Ni}$  is the Holstein condition [11], according to which  $J < W_H/3$  (see Table I), where  $J(T) \approx 0.67hv_{\text{ph}}(T/\theta_D)^{1/4}$  is the width of the polaron band at  $T = 300$  K.

The temperature dependences of the MR effect of  $\text{La}_{0.6}\text{Sr}_{0.15}\text{Bi}_{0.15}\text{Mn}_{1.1-x}\text{B}_x\text{O}_{3-\delta}$  ceramics with  $B = \text{Cr}, \text{Fe}, \text{Co}$  and  $\text{Ni}$  shown in Fig. 3. In all compositions with  $B = \text{Cr}$  ( $x = 0.15-0.3$ ),  $\text{Fe}$  ( $x = 0.05-0.3$ ),  $\text{Co}$  ( $x = 0.1-0.3$ ), and  $\text{Ni}$  ( $x = 0.2-0.3$ ), the peak of the MR effect appears in the temperature range  $T_p = 192-203$  K,  $T_p = 100-153$  K,  $T_p = 160-203$  K and  $T_p \approx 150$  K, respectively. The  $MR(T_p)$  value decreases with increasing concentration  $x$  and is in the intervals  $MR(T_p) = 5.9-7.5\%$  for  $B = \text{Cr}$ ,  $1.9-13.3\%$  for  $B = \text{Fe}$ ,  $5.4-8.9\%$  for  $B = \text{Co}$  and  $5\%$  for  $B = \text{Ni}$ . This type of the MR effect at  $T_p$  is connected with the scattering process of spin-polarized charge transport on the intercrystalline magnetic inhomogeneities of the defect structure containing impurity ions  $\text{Cr}^{3+}, \text{Fe}^{3+}, \text{Co}^{2+}$  ( $\text{Co}^{\text{III}}$ ) and  $\text{Ni}^{2+}$  as well as anionic  $\text{V}^{(a)}$  and cationic  $\text{V}^{(c)}$  vacancies. The absence of a peak in the  $MR(T)$  dependencies at  $T_p$  for other compositions is connected with a small crystallite size  $\leq 1 \mu\text{m}$  (see Fig. 4).

TABLE I. COMPARATIVE ANALYSIS OF THE TRANSPORT ( $E_\rho, \theta_D, v_{\text{ph}}$ ,  $W_H, \gamma_{\text{ph}}, J, r_p$ ) AND DIELECTRIC ( $\epsilon'$ ) PARAMETRS OF THE STUDIED  $\text{La}_{0.6}\text{Sr}_{0.15}\text{Bi}_{0.15}\text{Mn}_{1.1-x}\text{B}_x\text{O}_{3-\delta}$  CERAMICS WITH  $B = \text{Cr}, \text{Fe}, \text{Co}$  AND  $\text{Ni}$ .

$B$	$x$	$E_\rho, \text{meV}$	$\theta_D, \text{K}$	$v_{\text{ph}}, \text{T Hz}$	$r_p, \text{\AA}$	$\epsilon'$	$J, \text{meV}$	$W_H/3, \text{meV}$	$\gamma$
Mn	0	180	594	12.7	1.8	6.4	28.9	60.1	7.1
Cr	0.2	205	606	12.6	1.7	6.8	29.3	65.7	7.5
	0.3	206	600	12.5	1.6	7.6	29.1	65.7	7.6
Fe	0.2	181	500	11.3	1.8	7.3	25.4	54.7	7.6
	0.3	177	458	10.0	2.0	6.8	23.8	50.7	7.7
Co	0.2	171	552	11.5	1.9	6.8	27.4	53.8	6.8
	0.3	167	540	11.2	2.1	6.7	26.9	49.6	6.4
Ni	0.2	167	612	12.7	2.1	6.3	29.6	48.5	5.5
	0.3	157	580	12.1	2.4	6.1	28.4	42.4	5.1

In the low-temperature region at  $T \approx 77$  K, a tunneling type of the MR effect is observed for all compounds, which is due to the tunneling processes through the intercrystalline boundaries [12]. The magnitude of this MR effect depends on the size of the crystallites  $D$ , the composition and the extent of the intercrystalline zones and is in the intervals  $MR(77 \text{ K}) = 15.2-17.2\%$  for  $B = \text{Cr}$ ,  $1.8-15.3\%$  for  $B = \text{Fe}$ ,  $10.1-15.3\%$  for  $B = \text{Co}$  and  $9.4-15.3\%$  for  $B = \text{Ni}$ . For all compositions with  $B = \text{Cr}$ ,  $MR(77 \text{ K})$  and crystallite size  $D \approx 1 \mu\text{m}$  practically do not change (see Fig. 3 and 4). For other compositions with  $B = \text{Fe}, \text{Co}$ , and  $\text{Ni}$ ,  $MR(77 \text{ K})$  decreases with increasing  $x$ , and the crystallite size increases to  $D \approx 2-2.5 \mu\text{m}$ . An increase in the size of the crystallites  $D$ , which leads to a decrease in the extent of the intercrystalline zones, causes a decrease in the MR effect of the tunnel type [6].

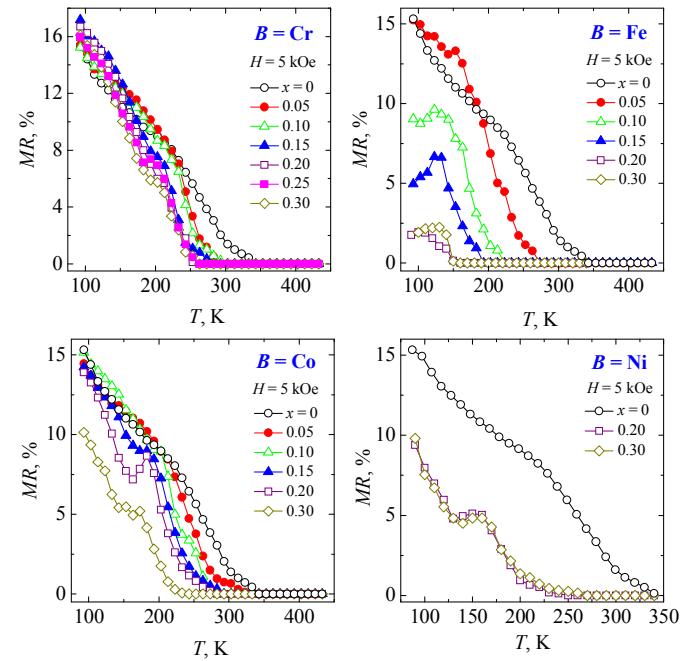


Fig. 3. Temperature dependences of the magnetoresistance effect in the field  $H = 5 \text{ kOe}$  of  $\text{La}_{0.6}\text{Sr}_{0.15}\text{Bi}_{0.15}\text{Mn}_{1.1-x}\text{B}_x\text{O}_{3-\delta}$  ceramics with  $B = \text{Cr}, \text{Fe}, \text{Co}, \text{Ni}$ .

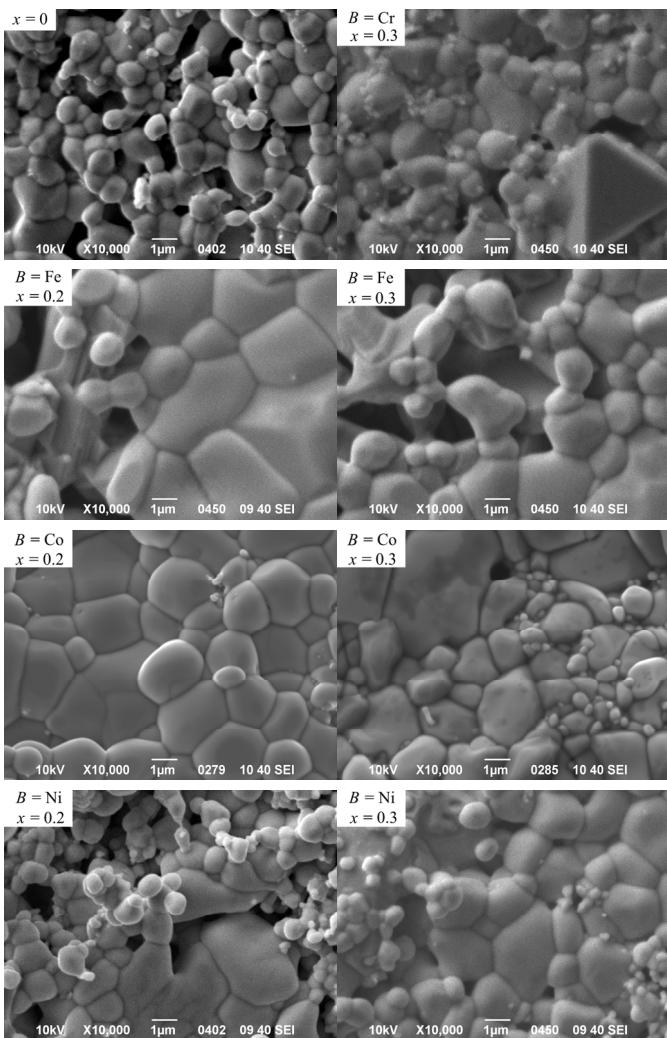


Fig. 4. Microstructure of  $\text{La}_{0.6}\text{Sr}_{0.15}\text{Bi}_{0.15}\text{Mn}_{1.1-x}\text{B}_x\text{O}_{3-\delta}$  ceramics with  $B = \text{Cr}, \text{Fe}, \text{Co}$  and  $\text{Ni}$  (SEM method).

It should be noted that the compositions with  $\text{Fe}$  ( $x = 0.05$ ) and  $\text{Cr}$  ( $x = 0.15$ ) have the highest values of the MR effect  $MR = 13.3\%$  at  $T = T_p$  and  $MR = 17.2\%$  at  $T = 77 \text{ K}$ , respectively.

#### IV. CONCLUSIONS

All ceramic samples  $\text{La}_{0.6}\text{Sr}_{0.15}\text{Bi}_{0.15}\text{Mn}_{1.1-x}\text{B}_x\text{O}_{3-\delta}$  with  $B = \text{Cr}, \text{Fe}, \text{Co}$  and  $\text{Ni}$  were single-phase and contain the  $R\bar{3}c$  rhombohedral distorted perovskite structure for all concentration range  $x$ . It has been established that the real perovskite structure contains cationic  $\text{V}^{(c)}$  and anionic  $\text{V}^{(a)}$  vacancies, concentrations of which are increased with increase in  $x$ .

For all compositions with increasing  $x$ , an increase in the resistivity  $\rho$  and the absence of a metal-semiconductor phase transition for  $x > 0.2$  are observed, which is caused by the weakening of the double exchange of  $\text{Mn}^{3+} \leftrightarrow \text{O}^{2-} \leftrightarrow \text{Mn}^{4+}$  by point defects of the vacancy type and  $3d$ -ions of the transition metals.

Using the small polaron hopping model, the electron-phonon interaction constant has been determined. It has been established that for all compounds a strong electron-phonon interaction ( $\gamma_{ph} > 4$ ) is observed, which leads to a partial localization of  $e_g$ -electrons  $\text{Mn}^{3+}$  and is well correlated with data of the temperature dependences  $\rho(T)$ . The iron ions, for which the electron-phonon interaction constant achieves maximum values, have the strongest effect on the change in magnetotransport properties.

It has been established that the compositions with  $\text{Fe}$  ( $x = 0.05$ ) and  $\text{Cr}$  ( $x = 0.15$ ) have the highest values of MR effect  $MR(T_p) = 13.3\%$  and  $MR(77 \text{ K}) = 17.2\%$ , respectively.

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#### REFERENCES

- [1] M. Opel "Spintronic oxides grown by laser-MBE," J. Phys. D: Appl. Phys. Vol. 45, pp. 033001 (31pp), 2012.
- [2] S.K. Barik, R. Mahendiran "Effect of Bi Doping on Magnetoresistance in  $\text{La}_{0.7-x}\text{Bi}_x\text{Sr}_0.3\text{MnO}_3$ ," J. Nanoscience and Nanotech. Vol. 11, pp. 2603–2606, 2011.
- [3] N. Nedelko, S. Lewinska, A. Pashchenko, I. Radelytskyi, R. Diduszko, E. Zubov, W. Lisowski, J.W. Sobczak, K. Dyakonov, A. S'law ska-Waniewska, V. Dyakonov, H. Szymczak "Magnetic properties and magnetocaloric effect in  $\text{La}_{0.7}\text{Sr}_{0.3-x}\text{Bi}_x\text{MnO}_3$  manganites," Journ. Alloys and Comp. Vol. 640, pp. 433-439, 2015.
- [4] I.O. Troyanchuk, O.S. Mantiuk, H. Szymczak, M.Yu. Shvedun "Magnetic phase transitions in the system  $\text{La}_{1-x}\text{Bi}_x\text{MnO}_3+\lambda$ ," Low Temp. Phys. Vol. 28, pp. 569-573, 2002.
- [5] O.S. Mantiuk, I.O. Troyanchuk, A.N. Chobot, H. Szymczak "Magnetic phase diagram of the manganites  $\text{Bi}_{1-x}\text{Sr}_x\text{MnO}_3$ ," Low Temp. Phys. Vol. 30, pp. 218-224, 2004.
- [6] A.V. Pashchenko, V.P. Pashchenko, V.K. Prokopenko, V.A. Turchenko, Yu.F. Revenko, A.S. Mazur, V.Ya. Sycheva, N.A. Liedienov, V.G. Pitsyuga, G.G. Levchenko "Role of Structure Imperfection in the Formation of the Magnetotransport Properties of Rare-Earth Manganites with a Perovskite Structure," J. Exp. Theor. Phys. Vol. 124, pp. 100-113, 2017.
- [7] A.M. Ahmed, M.A. Abedellateef, H.A. Abd El-Ghanny, A. Mohamed Abd El Mo'ez "Enhanced low-field magnetoresistance of  $\text{La}_{0.7}\text{Sr}_{0.3}\text{Mn}_{1-x}\text{Ni}_x\text{O}_3$  compounds by annealing process," Phys. Status Solidi A. Vol. 212, pp. 623-631, 2015.
- [8] N.F. Mott, E.A. Davis "Electronics process in non crystalline materials," Oxford : Clarendon Press, 2012. P. 608.
- [9] B.C. Zhao, W.H. Song, Y.Q. Ma, R.L. Zhang, J. Yang, Z.G. Sheng, W.J. Lu, J.M. Dai, Y.P. Sun "Magnetic and transport properties of the Co-doped manganite  $\text{La}_{0.7}\text{Sr}_{0.3}\text{Mn}_{1-x}\text{Co}_x\text{O}_3$  ( $0 \leq x \leq 0.5$ )," Phys. Stat. Sol. (b). Vol. 242, pp. 1719-1727, 2005.
- [10] Y.D. Zhang, T.L. Phan, D.S. Yang, S.C. Yu "Local structure and magnetocaloric effect for  $\text{La}_{0.7}\text{Sr}_{0.3}\text{Mn}_{1-x}\text{Ni}_x\text{O}_3$ ," Current Appl. Phys. Vol. 12, pp. 803-807, 2012.
- [11] T. Holstein "Studies of polaron motion: Part II. The "small" polaron," Ann. Phys. Vol. 8, pp. 343-389, 1959.
- [12] L.E. Hueso, J. Rivas, F. Rivadulla, M.A. Lopez-Quintela "Tuning of colossal magnetoresistance via grain size change in  $\text{La}_{0.67}\text{Ca}_{0.33}\text{MnO}_3$ ," J. Magn. Magn. Mater. Vol. 86, No. 7, p. 3881–3884, 1999.